MY6N80P

800V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

The MY6N80P is silicon N-channel Enhanced VDMOSFETs, obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy.

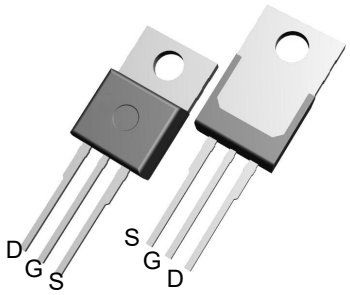
RoHS Compliant

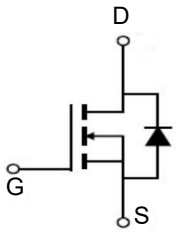
Features

V_{DSS}	800	V
I_D	6	A
P_D(T_C=25℃)	47	W
$R_{DS(ON)}$(atV_{GS} = 10V)	<2.5	Ω

Application

- High efficiency switch mode power supplies
- Power factor correction
- Electronic lamp ballast





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY6N80P	TO-220	MY6N80P	1000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain-Source Voltage		800	V
I_D	Drain Current	T_j=25℃	6	A
		T_j=100℃	3.8	
$V_{GS(TH)}$	Gate Threshold Voltage		±30	V
E_{AS}	Single Pulse Avalanche Energy (note1)		590	mJ
I_{AR}	Avalanche Current (note2)		5	A
P_D	Power Dissipation (Tj=25℃)		47	W
T_j	Junction Temperature(Max)		150	℃
T_{stg}	Storage Temperature		-55~+150	℃
TL	Maximum lead temperature for soldering purpose,1/8" from case for 5 seconds		300	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	-	2.66	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	-	62.5	℃/W

Electrical Characteristics (T_C=25 ℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA，V_{GS}=0	800	-	-	V
△BVDSS/ △TJ	Breakdown Voltage Temperature Coefficient	I_D=250μA ,Reference to 25℃	-	0.9	-	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=800V, V_{GS}=0V	-	-	10	μA
		V_{DS}=640V, Tj=125℃			100	
I_{GSSF}	Gate-body leakage Current, Forward	V_{GS}=+30V, V_{DS}=0V	-	-	100	nA
I_{GSSR}	Gate-body leakage Current, Reverse	V_{GS}=-30V, V_{DS}=0V	-	-	-100	
On Characteristics						
$V_{GS(TH)}$	Date Threshold Voltage	I_D=250μA,V_{DS}=V_{GS}	3	-	5	V
$R_{DS(ON)}$	Static Drain Source On-Resistance	I_D=3A,V_{GS}=10V	-	-	2.5	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	V_{DS}=25V， V_{GS}=0， f=1.0MHz	-	1230	-	pF
Coss	Output Capacitance		-	95	-	
Crss	Reverse Transfer Capacitance		-	11	-	
Switching Characteristics						
Td(on)	Turn-On Delay Time	V_{DD}=400V， I_D=6A R_G=25Ω (Note 3,4)	-	22	55	nS
Tr	Turn-On Rise Time		-	60	130	
Td(off)	Turn-Off Delay Time		-	55	120	
Tf	Turn-Off Rise Time		-	40	90	
Qg	Total Gate Charge	V_{DS}=640V,V_{GS}=10V， I_D=6A (Note 3,4)	-	31	-	nC
Qgs	Gate-Source Charge		-	5.6	-	
Qgd	Gate-Drain Charge		-	12	-	
Drain-Source Diode Characteristics and Maximum Ratings						
Is	Max. Diode Forward Current	-	-	-	6	A
I_{SM}	Max. Pulsed Forward Current	-	-	-	24	
V_{SD}	Diode Forward Voltage	I_D=6A	-	-	1.4	V
Trr	Reverse Recovery Time	I_S=6A,V_{GS} =0V diF/dt=100A/ μs (Note3)	610	-	-	nS
Qrr	Reverse Recovery Charge		4.7	-	-	μC

Notes : 1, L=11.1mH, IAS=6A, VDD=50V, RG=25Ω, Starting TJ =25°C
2, Repetitive Rating : Pulse width limited by maximum junction temperature
3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
4, Essentially Independent of Operating Temperature

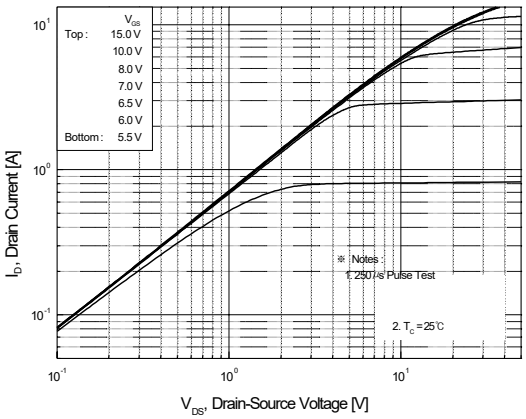


Figure 1. On-Region Characteristics

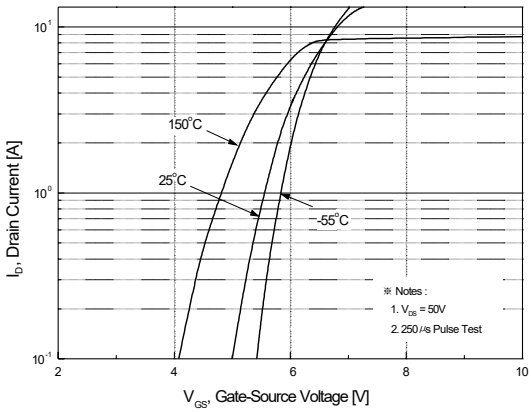


Figure 2. Transfer Characteristics

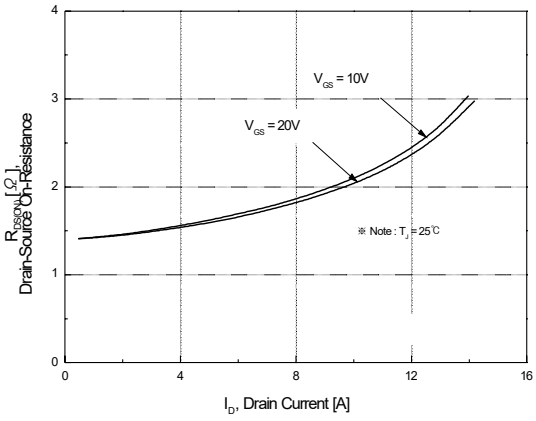


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

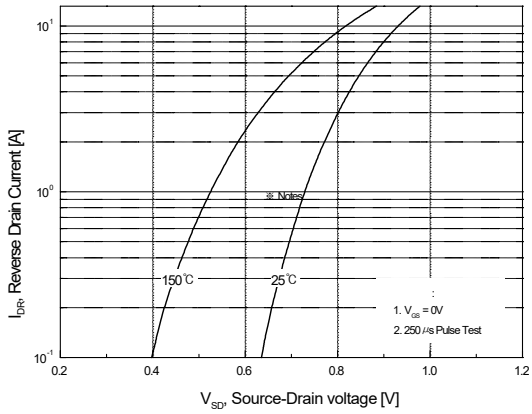


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

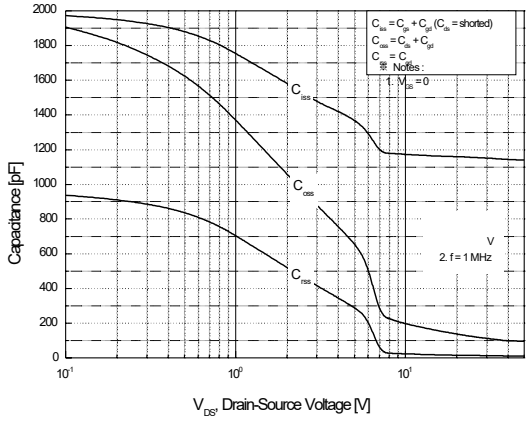


Figure 5. Capacitance Characteristics

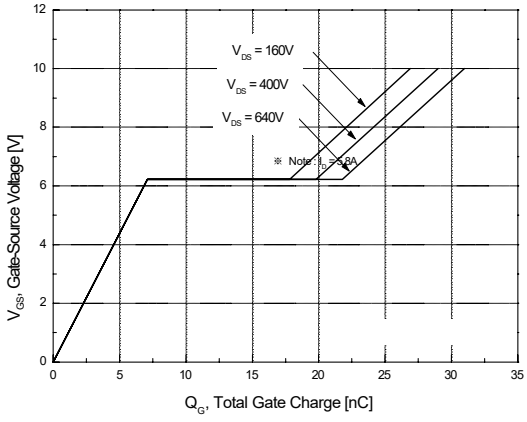


Figure 6. Gate Charge Characteristics

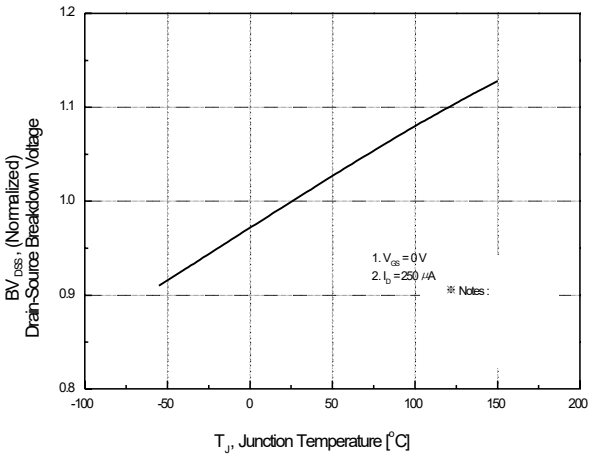


Figure 7. Breakdown Voltage Variation vs Temperature

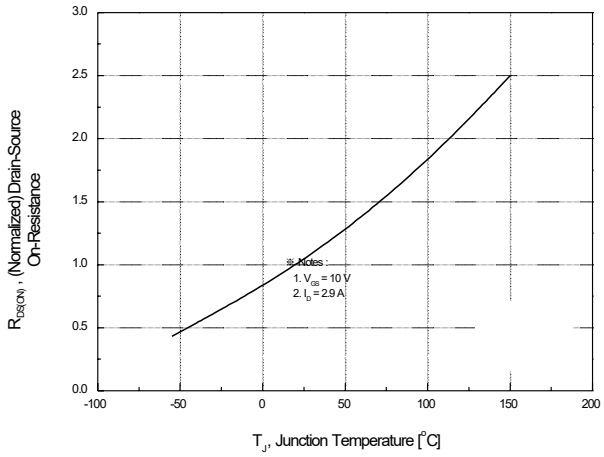


Figure 8. On-Resistance Variation vs Temperature

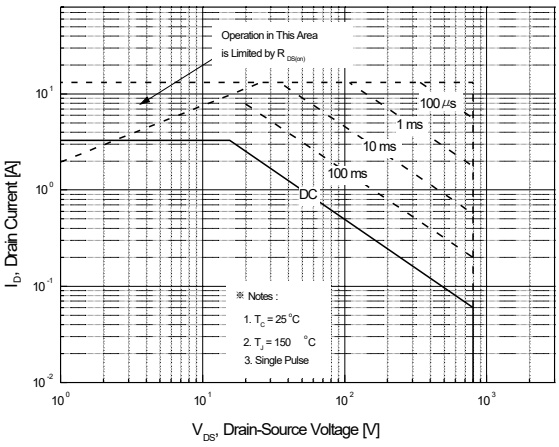


Figure 9. Maximum Safe Operating Area

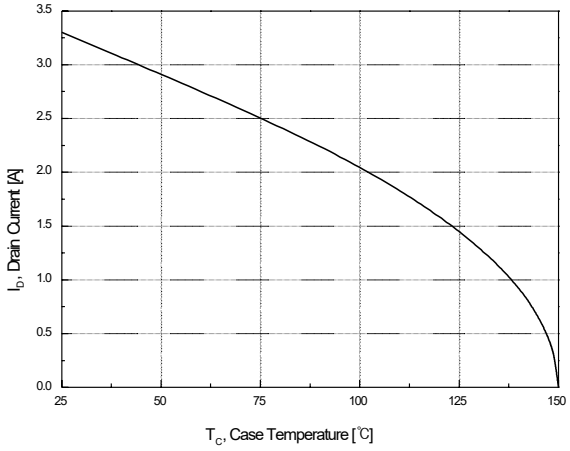


Figure 10. Maximum Drain Current vs Case Temperature

※ Notes

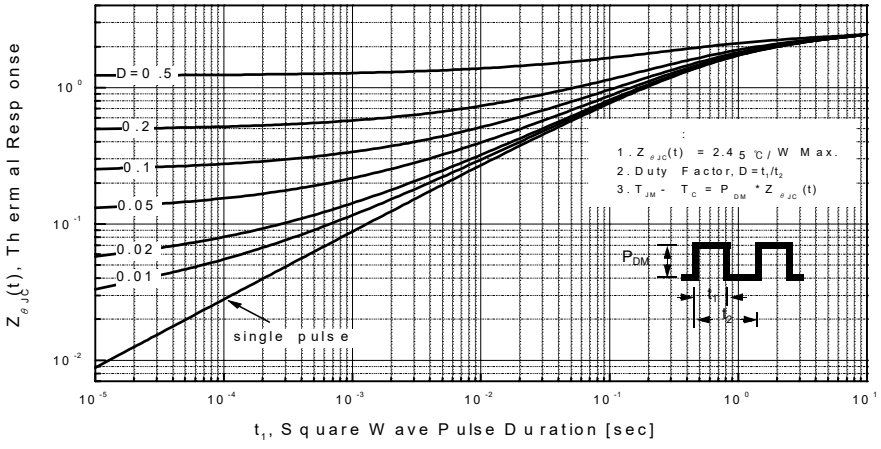
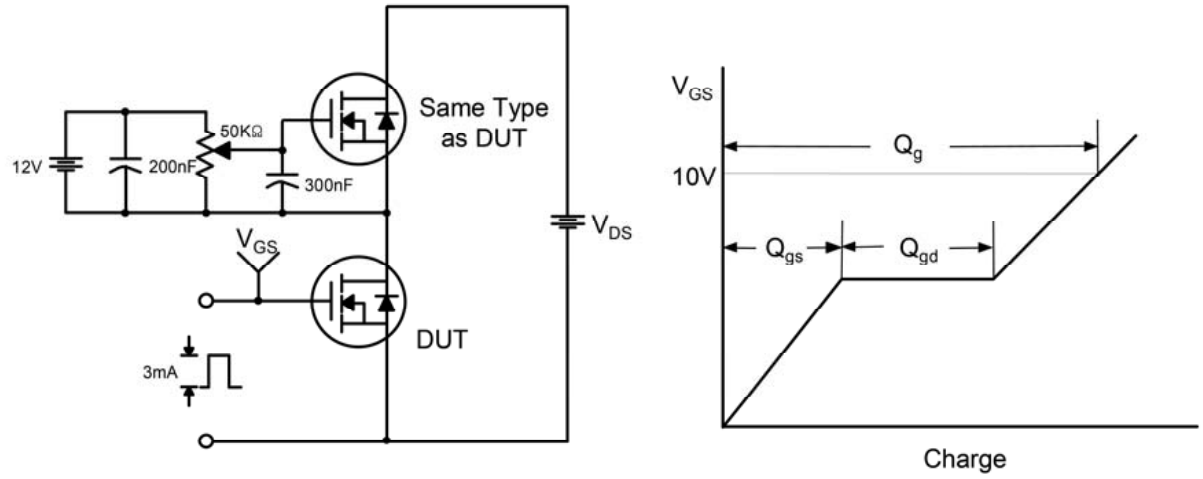
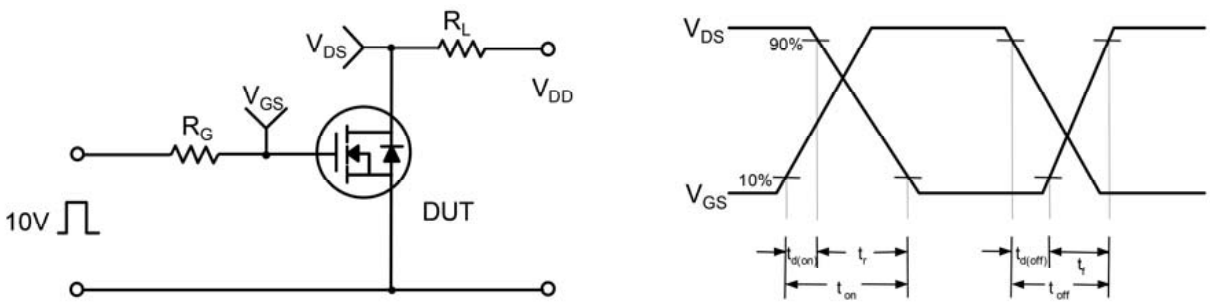


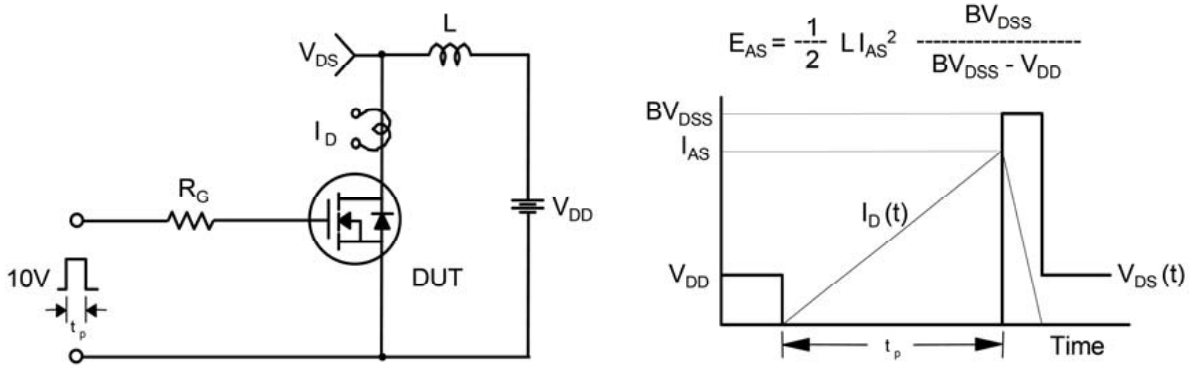
Figure 11. Transient Thermal Response Curve



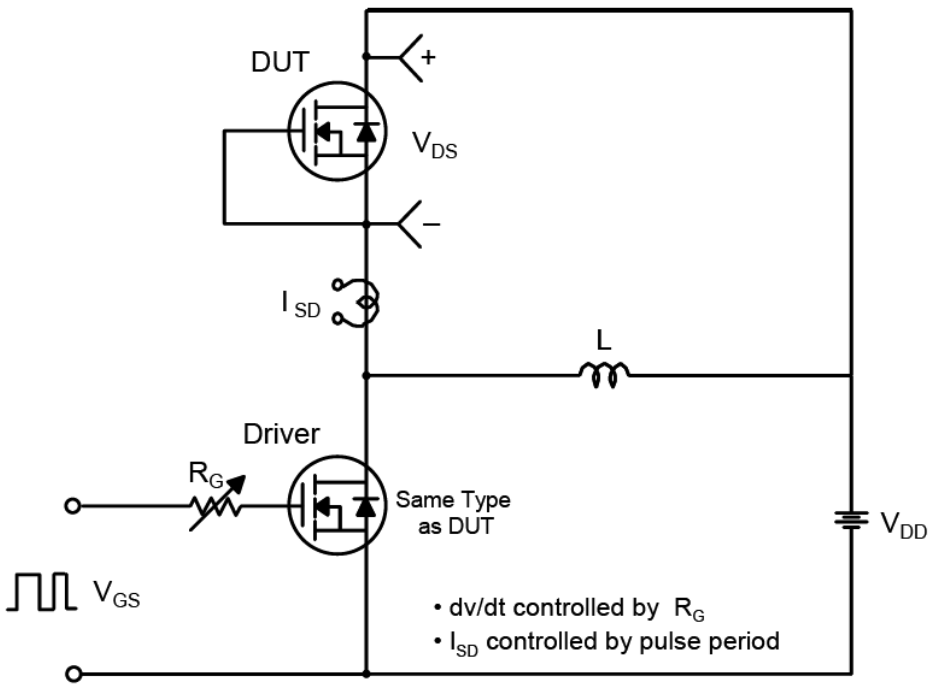
Resistive Switching Test Circuit & Waveforms

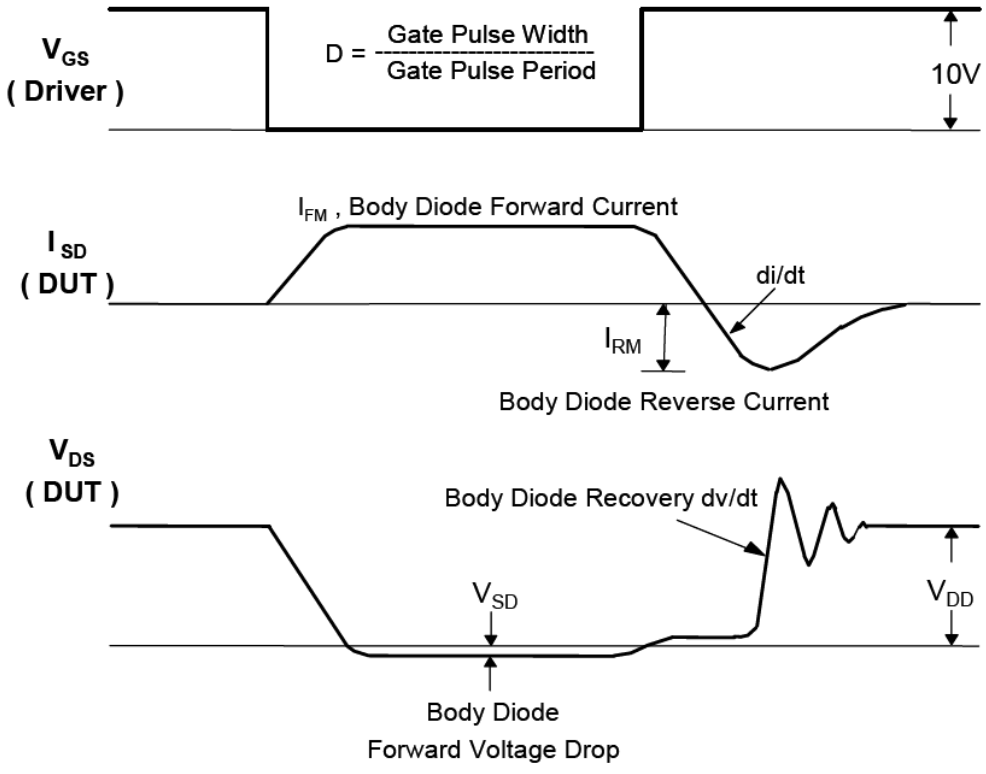


Unclamped Inductive Switching Test Circuit & Waveforms

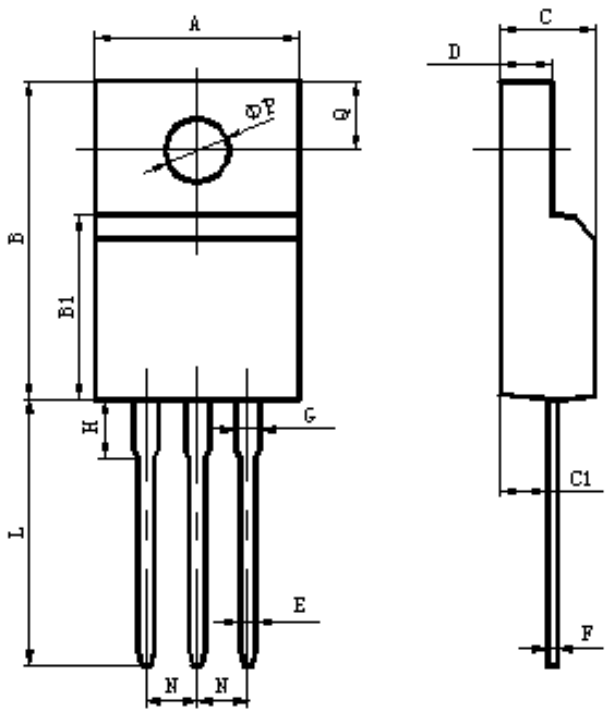


Peak Diode Recovery dv/dt Test Circuit & Waveform





Package Mechanical Data-TO-220 Single



Items	Values(mm)	
	MIN	MAX
A	9.60	10.4
B	15.4	16.2
B1	8.90	9.50
C	4.30	4.90
C1	2.10	3.00
D	2.40	3.00
E	0.60	1.00
F	0.30	0.60
G	1.12	1.42
H	3.40	3.80
	2.40	2.90
L*	12.0	14.0
N	2.34	2.74
Q	3.15	3.55
Φ P	2.90	3.30